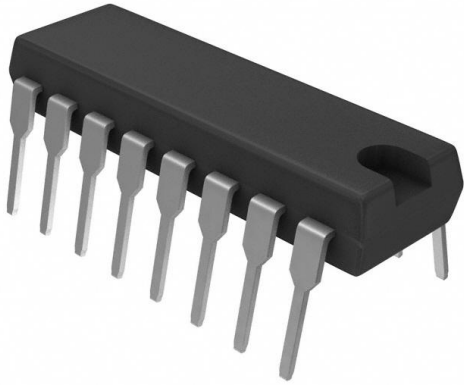


74LV4020N,112 Datasheet

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<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	74LV4020N,112-DG
Manufacturer	NXP USA Inc.
Manufacturer Product Number	74LV4020N,112
Description	IC BINARY COUNTER 14-BIT 16DIP
Detailed Description	Counter IC Binary Counter 1 Element 14 Bit Negative Edge 16-DIP



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RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

74LV4020N,112

Series:

74LV

Logic Type:

Binary Counter

Number of Elements:

1

Reset:

Asynchronous

Count Rate:

100 MHz

Voltage - Supply:

1 V ~ 5.5 V

Mounting Type:

Through Hole

Supplier Device Package:

16-DIP

Manufacturer:

NXP USA Inc.

Product Status:

Obsolete

Direction:

Up

Number of Bits per Element:

14

Timing:

-

Trigger Type:

Negative Edge

Operating Temperature:

-40°C ~ 125°C

Package / Case:

16-DIP (0.300", 7.62mm)

Base Product Number:

74LV4020

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8542.39.0001

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

74LV4020

14-stage binary ripple counter

Rev. 01 — 29 November 2005

Product data sheet

1. General description

The 74LV4020 is a low-voltage Si-gate CMOS device and is pin and function compatible with the 74HC4020 and 74HCT4020.

The 74LV4020 is a 14-stage binary ripple counter with a clock input (\overline{CP}), an overriding asynchronous master reset input (MR) and 12 fully buffered parallel outputs (Q0, and Q3 to Q13).

The counter advances on the HIGH-to-LOW transition of \overline{CP} . A HIGH on MR clears all counter stages and forces all outputs LOW, independent of the state of \overline{CP} .

Each counter stage is a static toggle flip-flop.

2. Features

- Optimized for low-voltage applications: 1.0 V to 5.5 V
- Accepts TTL input levels between $V_{CC} = 2.7$ V and $V_{CC} = 3.6$ V
- Typical LOW-level output voltage (peak) or output ground bounce: $V_{OL(p)} < 0.8$ V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- Typical HIGH-level output voltage (valley) or output V_{OH} undershoot: $V_{OH(v)} > 2$ V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-C exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V.
- Multiple package options
- Specified from -40 °C to $+80$ °C and from -40 °C to $+125$ °C.

3. Applications

- Frequency dividing circuits
- Time delay circuits
- Control counters

4. Quick reference data

Table 1: Quick reference data
 $GND = 0\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t_r = t_f = 2.5\text{ ns}.$

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{PHL}	propagation delay	$C_L = 15\text{ pF}; V_{CC} = 3.3\text{ V}$				
t_{PLH}	\overline{CP} to Q0		-	12	-	ns
	Qn to Q(n+1)		-	7	-	ns
t_{PHL}	propagation delay	$C_L = 15\text{ pF}; V_{CC} = 3.3\text{ V}$				
	MR to Qn		-	16	-	ns
f_{max}	maximum input clock frequency	$C_L = 15\text{ pF}; V_{CC} = 3.3\text{ V}$	-	100	-	MHz
C_i	input capacitance		-	3.5	-	pF
C_{PD}	power dissipation capacitance	per gate; $V_I = GND$ to V_{CC}	[1]	20	-	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$$
 where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

5. Ordering information

Table 2: Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LV4020N	-40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74LV4020D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74LV4020DB	-40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74LV4020PW	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

6. Functional diagram

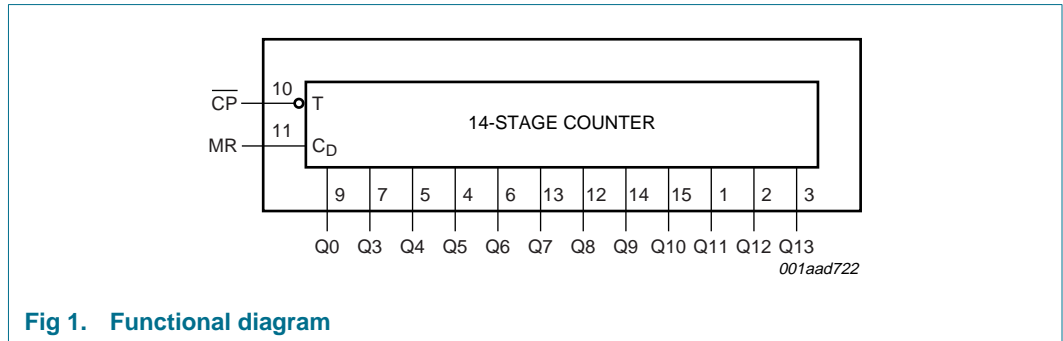


Fig 1. Functional diagram

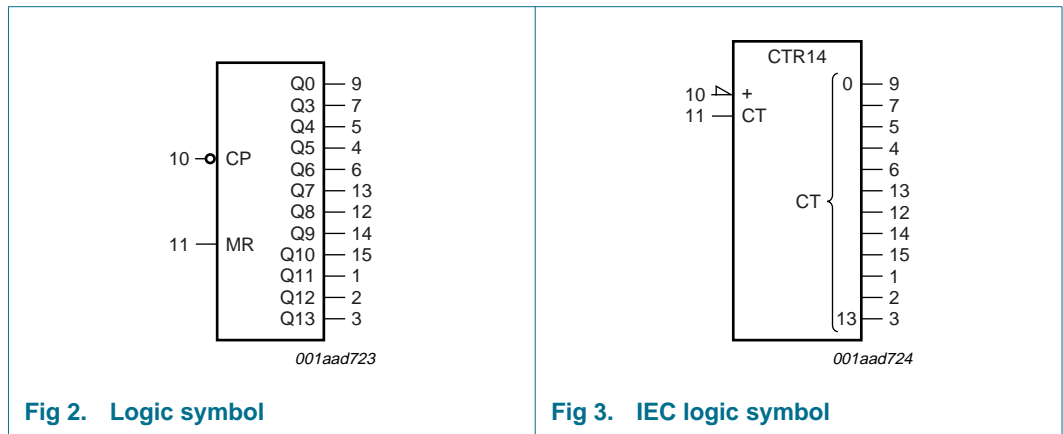


Fig 2. Logic symbol

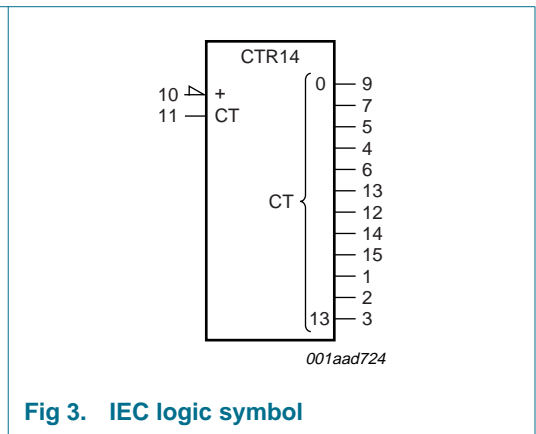


Fig 3. IEC logic symbol

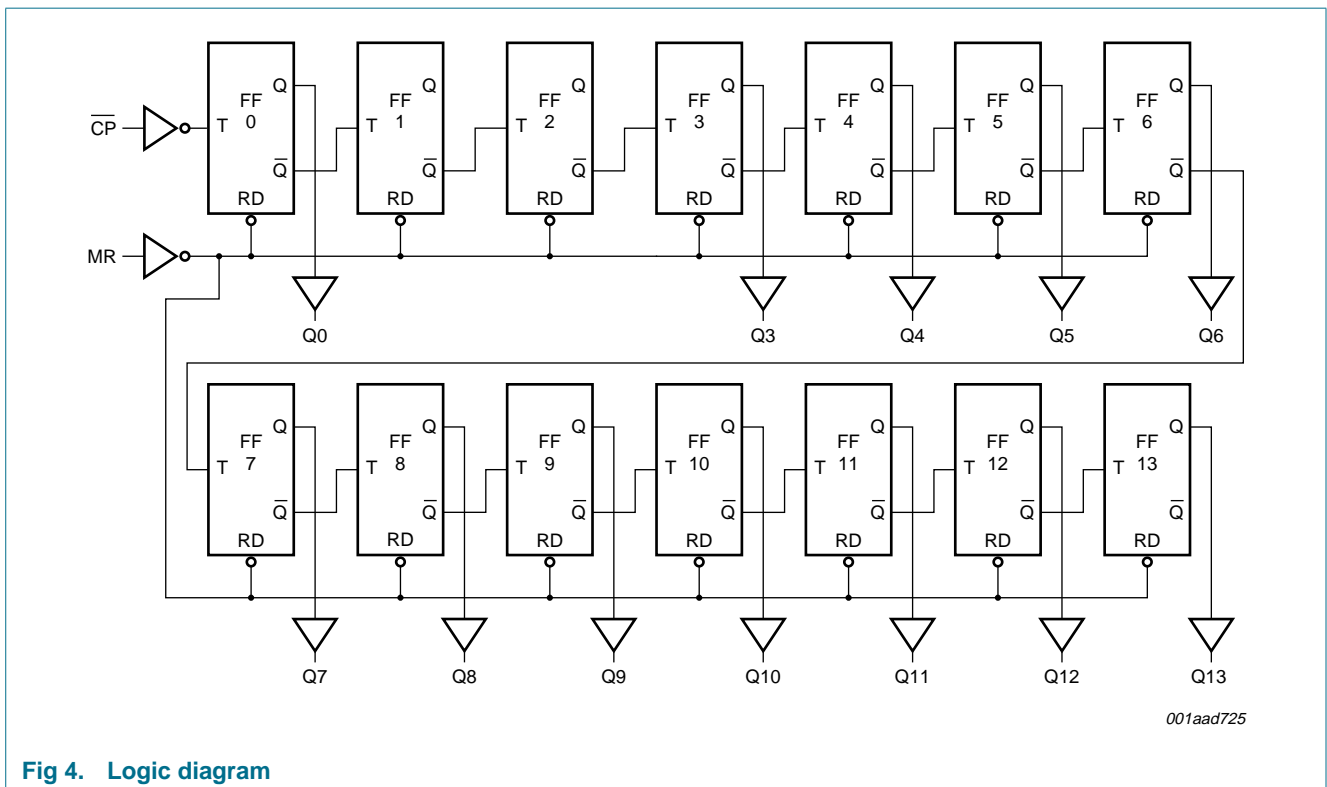
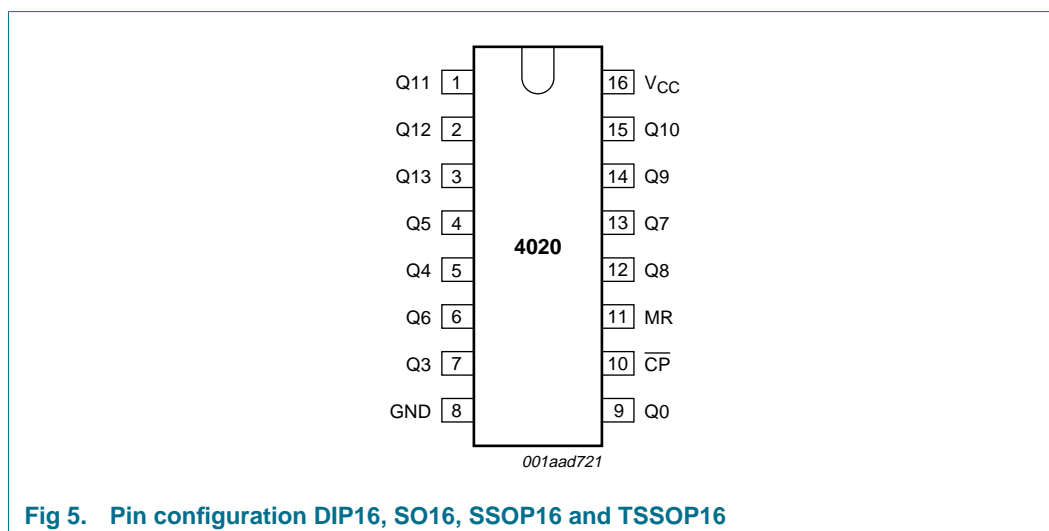


Fig 4. Logic diagram

7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3: Pin description

Symbol	Pin	Description
Q11	1	parallel output 11
Q12	2	parallel output 12
Q13	3	parallel output 13
Q5	4	parallel output 5
Q4	5	parallel output 4
Q6	6	parallel output 6
Q3	7	parallel output 3
GND	8	ground (0 V)
Q0	9	parallel output 0
\overline{CP}	10	clock input (HIGH-to-LOW, edge-triggered)
MR	11	master reset input (active HIGH)
Q8	12	parallel output 8
Q7	13	parallel output 7
Q9	14	parallel output 9
Q10	15	parallel output 10
V _{CC}	16	supply voltage

8. Functional description

8.1 Function table

Table 4: Function table [1]

Input		Output
CP	MR	Q0, Q3 to Q13
↑	L	no change
↓	L	count
X	H	L

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 ↑ = LOW-to-HIGH clock transition;
 ↓ = HIGH-to-LOW clock transition.

8.1.1 Timing diagram

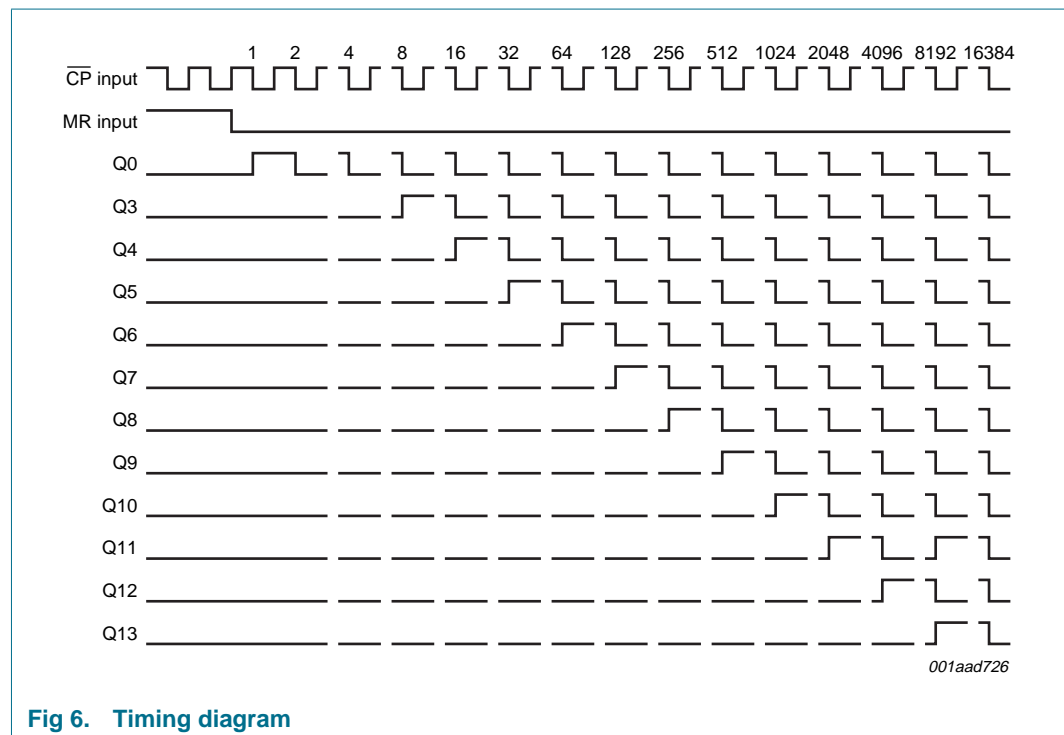


Fig 6. Timing diagram

9. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	± 50	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $V_{CC} + 0.5\text{ V}$	-	± 25	mA
I_{CC}	quiescent supply current		-	50	mA
I_{GND}	ground current		-	-50	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$			
	DIP16 package		[1] -	750	mW
	SO16 package		[2] -	500	mW
	SSOP16 and TSSOP16 packages		[3] -	400	mW

[1] Above $T_{amb} = 70\text{ °C}$: P_{tot} derates linearly with 12 mW/K.

[2] Above $T_{amb} = 70\text{ °C}$: P_{tot} derates linearly with 8 mW/K.

[3] Above $T_{amb} = 60\text{ °C}$: P_{tot} derates linearly with 5.5 mW/K.

10. Recommended operating conditions

Table 6: Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		[1] 1.0	3.3	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.0\text{ V}$ to 2.0 V	-	-	500	ns/V
		$V_{CC} = 2.0\text{ V}$ to 2.7 V	-	-	200	ns/V
		$V_{CC} = 2.7\text{ V}$ to 3.6 V	-	-	100	ns/V
		$V_{CC} = 3.6\text{ V}$ to 5.5 V	-	-	50	ns/V

[1] The static characteristics are guaranteed from $V_{CC} = 1.2\text{ V}$ to $V_{CC} = 5.5\text{ V}$, but LV devices are guaranteed to function down to $V_{CC} = 1.0\text{ V}$ (with input levels GND or V_{CC}).

11. Static characteristics

Table 7: Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40\text{ °C to }+85\text{ °C}$ [1]						
V_{IH}	HIGH-state input voltage	$V_{CC} = 1.2\text{ V}$	0.9	-	-	V
		$V_{CC} = 2.0\text{ V}$	1.4	-	-	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	2.0	-	-	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	$0.7 \times V_{CC}$	-	-	V
V_{IL}	LOW-state input voltage	$V_{CC} = 1.2\text{ V}$	-	-	0.3	V
		$V_{CC} = 2.0\text{ V}$	-	-	0.6	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	0.8	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	$0.3 \times V_{CC}$	V
V_{OH}	HIGH-state output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100\text{ }\mu\text{A}; V_{CC} = 1.2\text{ V}$	-	1.2	-	V
		$I_O = -100\text{ }\mu\text{A}; V_{CC} = 2.0\text{ V}$	1.8	2.0	-	V
		$I_O = -100\text{ }\mu\text{A}; V_{CC} = 2.7\text{ V}$	2.5	2.7	-	V
		$I_O = -100\text{ }\mu\text{A}; V_{CC} = 3.0\text{ V}$	2.8	3.0	-	V
		$I_O = -100\text{ }\mu\text{A}; V_{CC} = 4.5\text{ V}$	4.3	4.5	-	V
		$I_O = -6\text{ mA}; V_{CC} = 3.0\text{ V}$	2.40	2.82	-	V
		$I_O = -12\text{ mA}; V_{CC} = 4.5\text{ V}$	3.60	4.20	-	V
V_{OL}	LOW-state output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100\text{ }\mu\text{A}; V_{CC} = 1.2\text{ V}$	-	0	-	V
		$I_O = 100\text{ }\mu\text{A}; V_{CC} = 2.0\text{ V}$	-	0	0.2	V
		$I_O = 100\text{ }\mu\text{A}; V_{CC} = 2.7\text{ V}$	-	0	0.2	V
		$I_O = 100\text{ }\mu\text{A}; V_{CC} = 3.0\text{ V}$	-	0	0.2	V
		$I_O = 100\text{ }\mu\text{A}; V_{CC} = 4.5\text{ V}$	-	0	0.2	V
		$I_O = 6\text{ mA}; V_{CC} = 3.0\text{ V}$	-	0.25	0.40	V
		$I_O = 12\text{ mA}; V_{CC} = 4.5\text{ V}$	-	0.35	0.55	V
I_{LI}	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5\text{ V}$	-	-	1.0	μA
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}; V_{CC} = 5.5\text{ V}$	-	-	20.0	μA
ΔI_{CC}	additional quiescent supply current	per input; $V_I = V_{CC} - 0.6\text{ V}; V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	500	μA
C_i	input capacitance		-	3.5	-	pF
$T_{amb} = -40\text{ °C to }+125\text{ °C}$						
V_{IH}	HIGH-state input voltage	$V_{CC} = 1.2\text{ V}$	0.9	-	-	V
		$V_{CC} = 2.0\text{ V}$	1.4	-	-	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	2.0	-	-	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	$0.7 \times V_{CC}$	-	-	V

Table 7: Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{IL}	LOW-state input voltage	V _{CC} = 1.2 V	-	-	0.3	V
		V _{CC} = 2.0 V	-	-	0.6	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3 × V _{CC}	V
V _{OH}	HIGH-state output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 μA; V _{CC} = 1.2 V	-	-	-	V
		I _O = -100 μA; V _{CC} = 2.0 V	1.8	-	-	V
		I _O = -100 μA; V _{CC} = 2.7 V	2.5	-	-	V
		I _O = -100 μA; V _{CC} = 3.0 V	2.8	-	-	V
		I _O = -100 μA; V _{CC} = 4.5 V	4.3	-	-	V
		I _O = -6 mA; V _{CC} = 3.0 V	2.20	-	-	V
		I _O = -12 mA; V _{CC} = 4.5 V	3.50	-	-	V
V _{OL}	LOW-state output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 μA; V _{CC} = 1.2 V	-	-	-	V
		I _O = 100 μA; V _{CC} = 2.0 V	-	-	0.2	V
		I _O = 100 μA; V _{CC} = 2.7 V	-	-	0.2	V
		I _O = 100 μA; V _{CC} = 3.0 V	-	-	0.2	V
		I _O = 100 μA; V _{CC} = 4.5 V	-	-	0.2	V
		I _O = 6 mA; V _{CC} = 3.0 V	-	-	0.50	V
		I _O = 12 mA; V _{CC} = 4.5 V	-	-	0.65	V
I _{LI}	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	1.0	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	160	μA
ΔI _{CC}	additional quiescent supply current	per input; V _I = V _{CC} - 0.6 V; V _{CC} = 2.7 V to 3.6 V	-	-	850	μA

[1] All typical values are measured at T_{amb} = 25 °C.

12. Dynamic characteristics

Table 8: Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF; for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40$ °C to $+85$ °C [1]						
t_{PHL} , t_{PLH}	propagation delay \overline{CP} to Q0	see Figure 7				
		$V_{CC} = 1.2$ V	-	60	-	ns
		$V_{CC} = 2.0$ V	-	27	43	ns
		$V_{CC} = 2.7$ V	-	19	31	ns
		$V_{CC} = 3.0$ V to 3.6 V	-	16	26	ns
		$V_{CC} = 4.5$ V to 5.5 V	-	11	17	ns
		$V_{CC} = 3.3$ V; $C_L = 15$ pF	-	12	-	ns
	Qn to Q(n+1)	see Figure 7				
		$V_{CC} = 1.2$ V	-	40	-	ns
		$V_{CC} = 2.0$ V	-	18	29	ns
		$V_{CC} = 2.7$ V	-	13	21	ns
		$V_{CC} = 3.0$ V to 3.6 V	-	11	18	ns
		$V_{CC} = 4.5$ V to 5.5 V	-	7	12	ns
		$V_{CC} = 3.3$ V; $C_L = 15$ pF	-	7	-	ns
t_{PHL}	propagation delay MR to Qn	see Figure 8				
		$V_{CC} = 1.2$ V	-	55	-	ns
		$V_{CC} = 2.0$ V	-	27	44	ns
		$V_{CC} = 2.7$ V	-	19	31	ns
		$V_{CC} = 3.0$ V to 3.6 V	-	16	26	ns
		$V_{CC} = 4.5$ V to 5.5 V	-	11	17	ns
		$V_{CC} = 3.3$ V; $C_L = 15$ pF	-	16	-	ns
t_W	pulse width \overline{CP} (HIGH and LOW)	see Figure 7				
		$V_{CC} = 2.0$ V	35	7	-	ns
		$V_{CC} = 2.7$ V	25	5	-	ns
		$V_{CC} = 3.0$ V to 3.6 V	20	4	-	ns
		$V_{CC} = 4.5$ V to 5.5 V	15	3	-	ns
	MR (HIGH)	see Figure 8				
		$V_{CC} = 2.0$ V	35	11	-	ns
		$V_{CC} = 2.7$ V	25	9	-	ns
		$V_{CC} = 3.0$ V to 3.6 V	20	8	-	ns
		$V_{CC} = 4.5$ V to 5.5 V	15	7	-	ns

Table 8: Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF; for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
t_{rec}	recovery time MR to $\overline{\text{CP}}$	see Figure 8					
		$V_{\text{CC}} = 1.2$ V	-	10	-	ns	
		$V_{\text{CC}} = 2.0$ V	22	5	-	ns	
		$V_{\text{CC}} = 2.7$ V	16	4	-	ns	
		$V_{\text{CC}} = 3.0$ V to 3.6 V	13	3	-	ns	
		$V_{\text{CC}} = 4.5$ V to 5.5 V	10	2	-	ns	
f_{max}	maximum input clock frequency	see Figure 7					
		$V_{\text{CC}} = 2.0$ V	14	60	-	MHz	
		$V_{\text{CC}} = 2.7$ V	19	76	-	MHz	
		$V_{\text{CC}} = 3.0$ V to 3.6 V	24	94	-	MHz	
		$V_{\text{CC}} = 4.5$ V to 5.5 V	36	112	-	MHz	
		$V_{\text{CC}} = 3.3$ V; $C_L = 15$ pF	-	100	-	MHz	
C_{PD}	power dissipation capacitance	per gate; $V_I = \text{GND to } V_{\text{CC}}$	2 -	20	-	pF	
$T_{\text{amb}} = -40$ °C to $+125$ °C							
t_{PHL} , t_{PLH}	propagation delay $\overline{\text{CP}}$ to Q0	see Figure 7					
		$V_{\text{CC}} = 1.2$ V	-	-	-	ns	
		$V_{\text{CC}} = 2.0$ V	-	-	54	ns	
		$V_{\text{CC}} = 2.7$ V	-	-	38	ns	
		$V_{\text{CC}} = 3.0$ V to 3.6 V	-	-	32	ns	
		$V_{\text{CC}} = 4.5$ V to 5.5 V	-	-	22	ns	
		Qn to Q(n+1)	see Figure 7				
			$V_{\text{CC}} = 1.2$ V	-	-	-	ns
			$V_{\text{CC}} = 2.0$ V	-	-	37	ns
			$V_{\text{CC}} = 2.7$ V	-	-	26	ns
			$V_{\text{CC}} = 3.0$ V to 3.6 V	-	-	22	ns
$V_{\text{CC}} = 4.5$ V to 5.5 V	-		-	15	ns		
t_{PHL}	propagation delay MR to Qn	see Figure 8					
		$V_{\text{CC}} = 1.2$ V	-	-	-	ns	
		$V_{\text{CC}} = 2.0$ V	-	-	55	ns	
		$V_{\text{CC}} = 2.7$ V	-	-	39	ns	
		$V_{\text{CC}} = 3.0$ V to 3.6 V	-	-	32	ns	
		$V_{\text{CC}} = 4.5$ V to 5.5 V	-	-	22	ns	

Table 8: Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF; for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
t_W	pulse width						
		\overline{CP} (HIGH and LOW)	see Figure 7				
			$V_{CC} = 2.0$ V	41	-	-	ns
			$V_{CC} = 2.7$ V	30	-	-	ns
			$V_{CC} = 3.0$ V to 3.6 V	24	-	-	ns
			$V_{CC} = 4.5$ V to 5.5 V	18	-	-	ns
		MR (HIGH)	see Figure 8				
			$V_{CC} = 2.0$ V	41	-	-	ns
			$V_{CC} = 2.7$ V	30	-	-	ns
			$V_{CC} = 3.0$ V to 3.6 V	24	-	-	ns
		$V_{CC} = 4.5$ V to 5.5 V	18	-	-	ns	
t_{rec}	recovery time						
		MR to \overline{CP}	see Figure 8				
			$V_{CC} = 1.2$ V	-	-	-	ns
			$V_{CC} = 2.0$ V	26	-	-	ns
			$V_{CC} = 2.7$ V	19	-	-	ns
			$V_{CC} = 3.0$ V to 3.6 V	15	-	-	ns
		$V_{CC} = 4.5$ V to 5.5 V	12	-	-	ns	
f_{max}	maximum input clock frequency	see Figure 7					
			$V_{CC} = 2.0$ V	12	-	-	MHz
			$V_{CC} = 2.7$ V	16	-	-	MHz
			$V_{CC} = 3.0$ V to 3.6 V	20	-	-	MHz
			$V_{CC} = 4.5$ V to 5.5 V	30	-	-	MHz

[1] Typical values are measured at nominal V_{CC} and $T_{amb} = 25$ °C.

[2] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

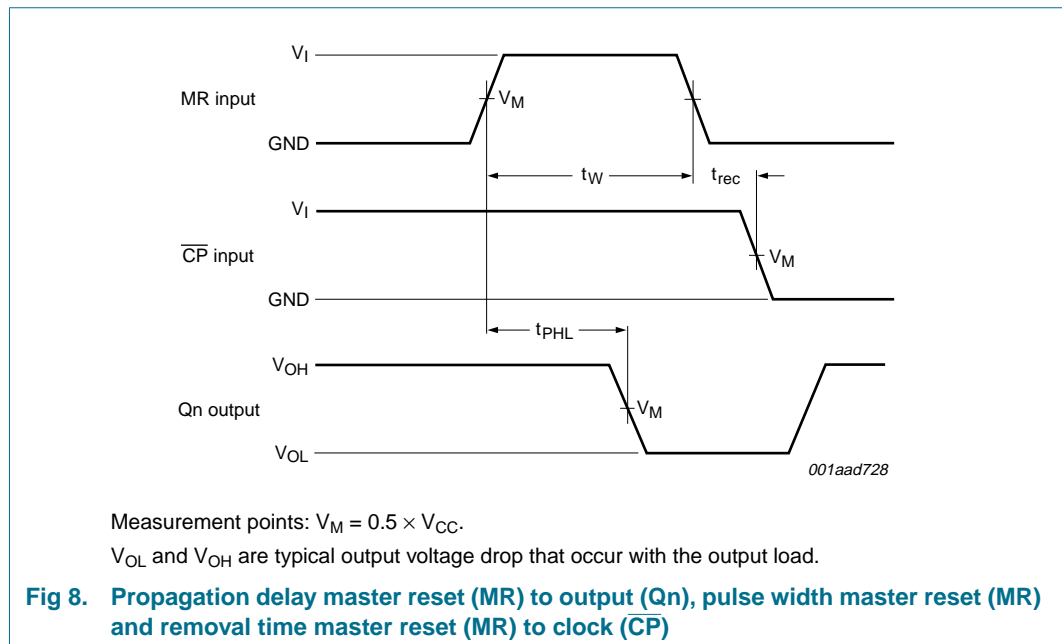
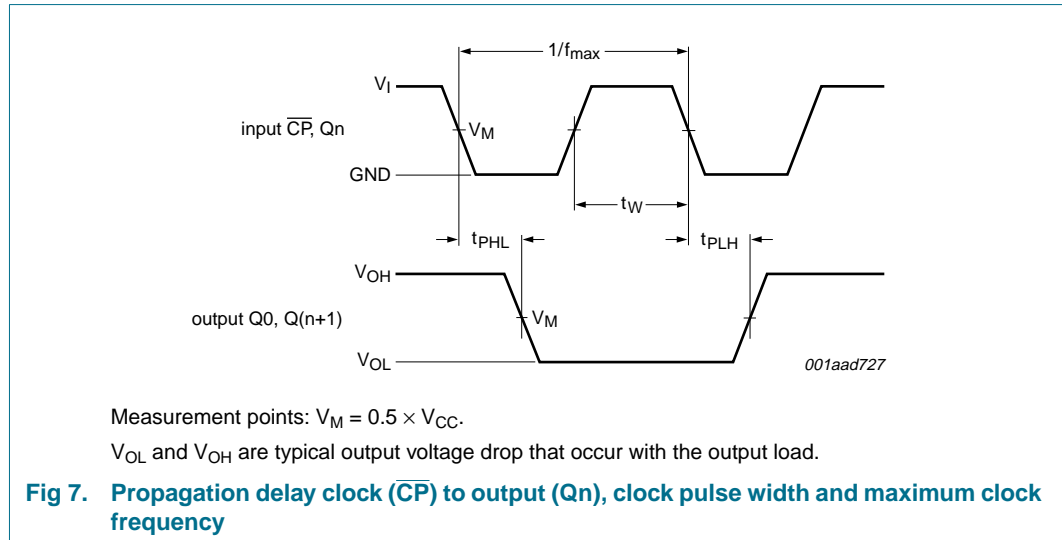
C_L = output load capacitance in pF;

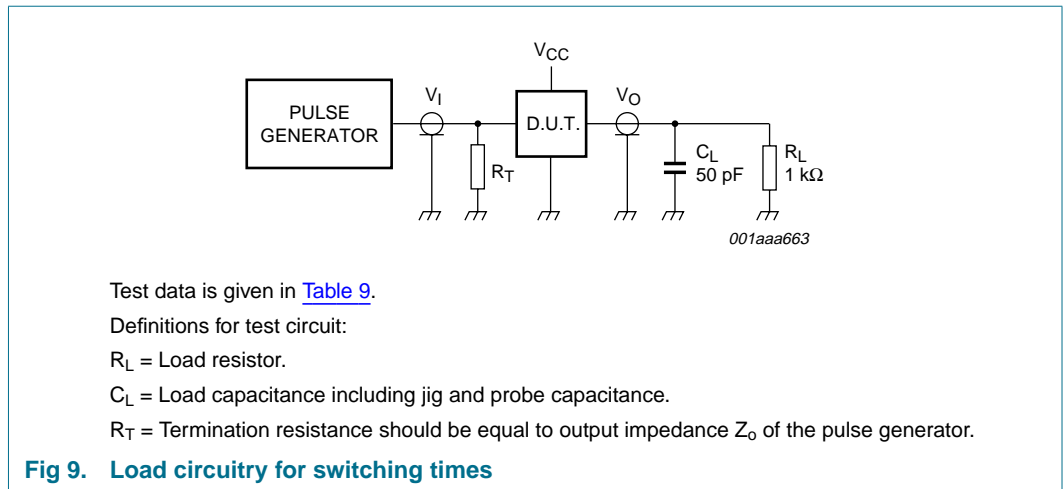
V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

13. Waveforms



**Table 9: Test data**

Supply voltage	Input		Load		Test
V_{CC}	V_I	t_r, t_f	C_L	R_L	
1.2 V	V_{CC}	≤ 2.5 ns	50 pF	1 kΩ	t_{PHL}, t_{PLH}
2.0 V	V_{CC}	≤ 2.5 ns	50 pF	1 kΩ	t_{PHL}, t_{PLH}
2.7 V	2.7 V	≤ 2.5 ns	50 pF	1 kΩ	t_{PHL}, t_{PLH}
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF, 15 pF	1 kΩ	t_{PHL}, t_{PLH}
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	1 kΩ	t_{PHL}, t_{PLH}

14. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4

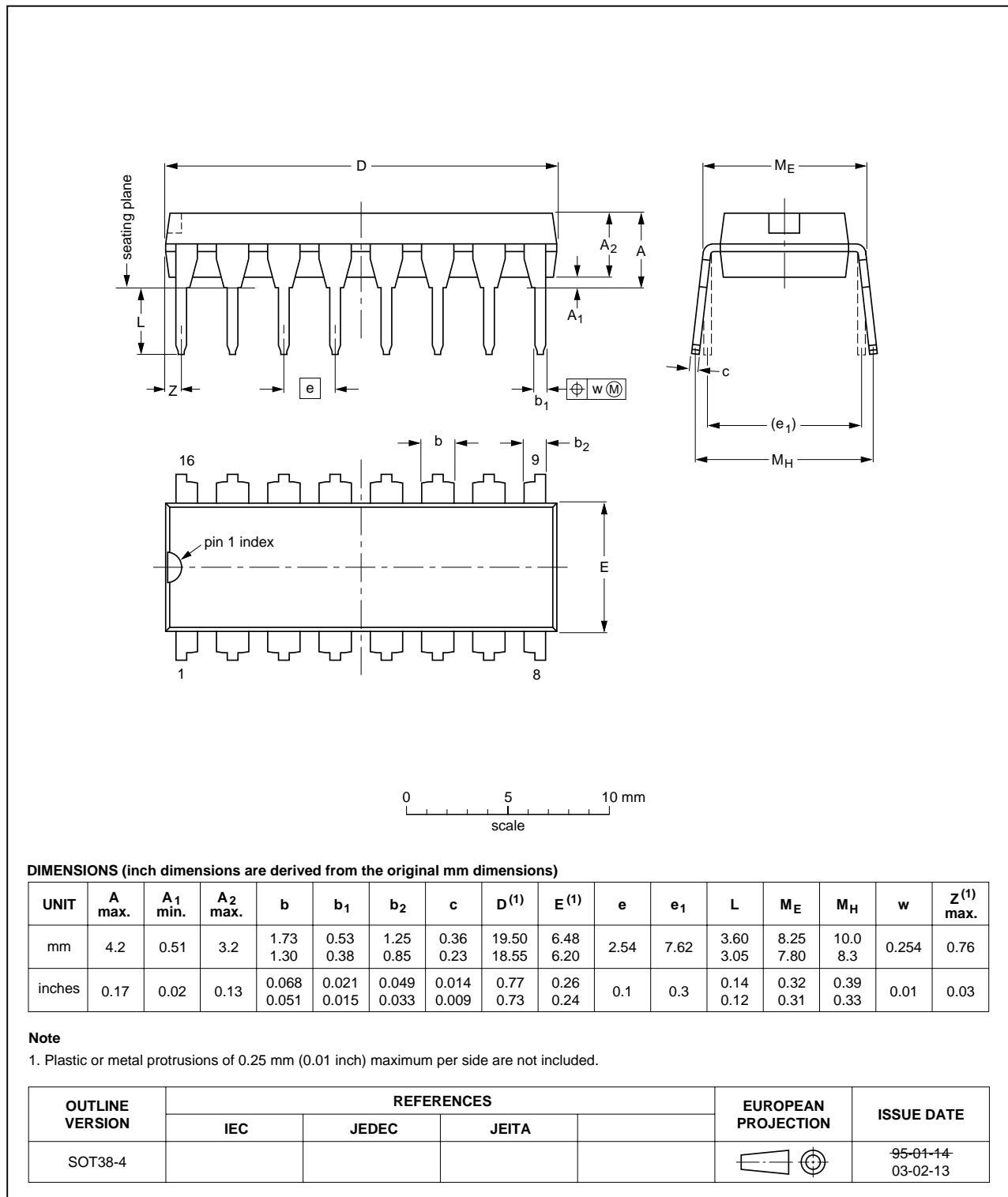


Fig 10. Package outline SOT38-1 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

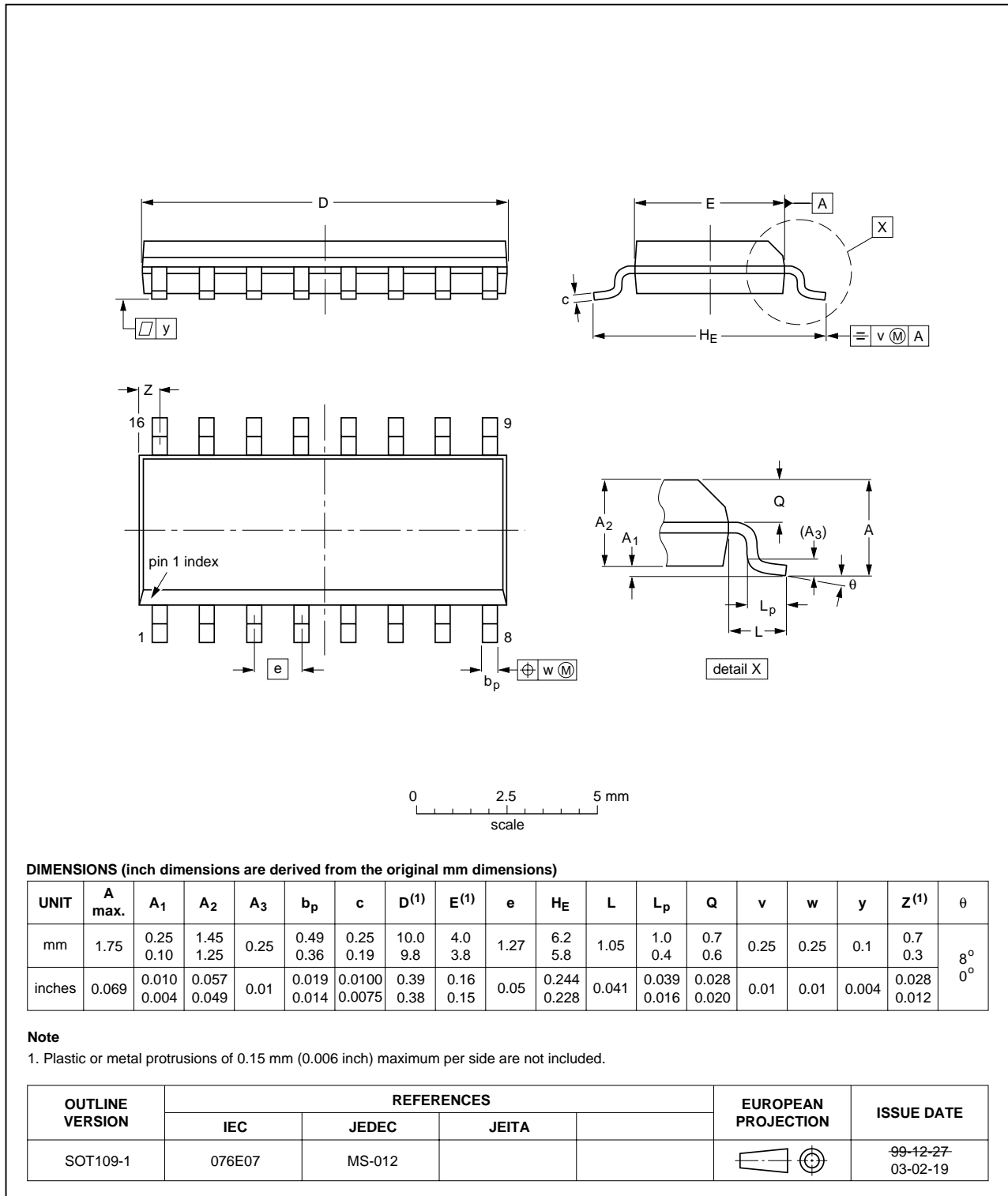


Fig 11. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

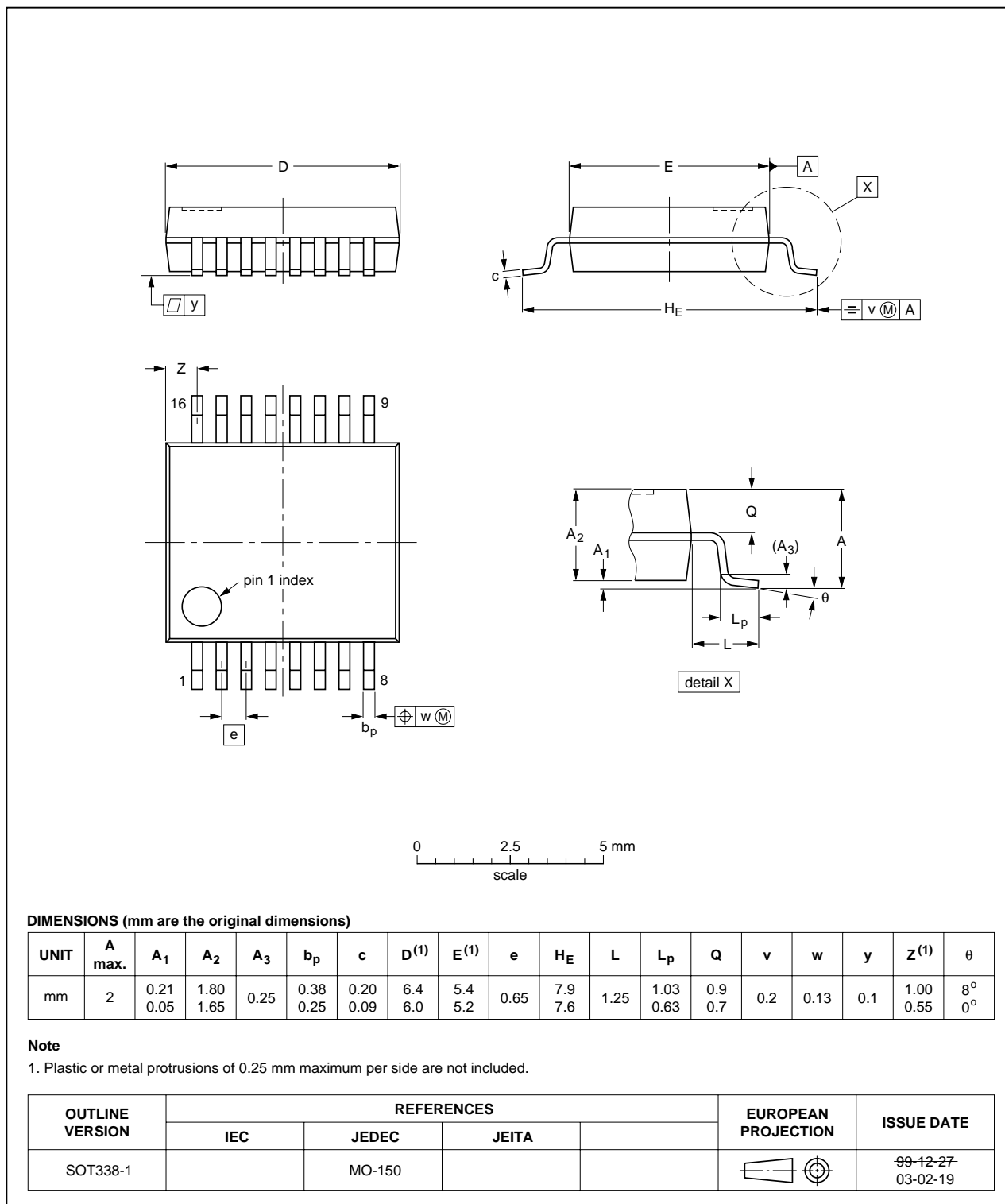


Fig 12. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

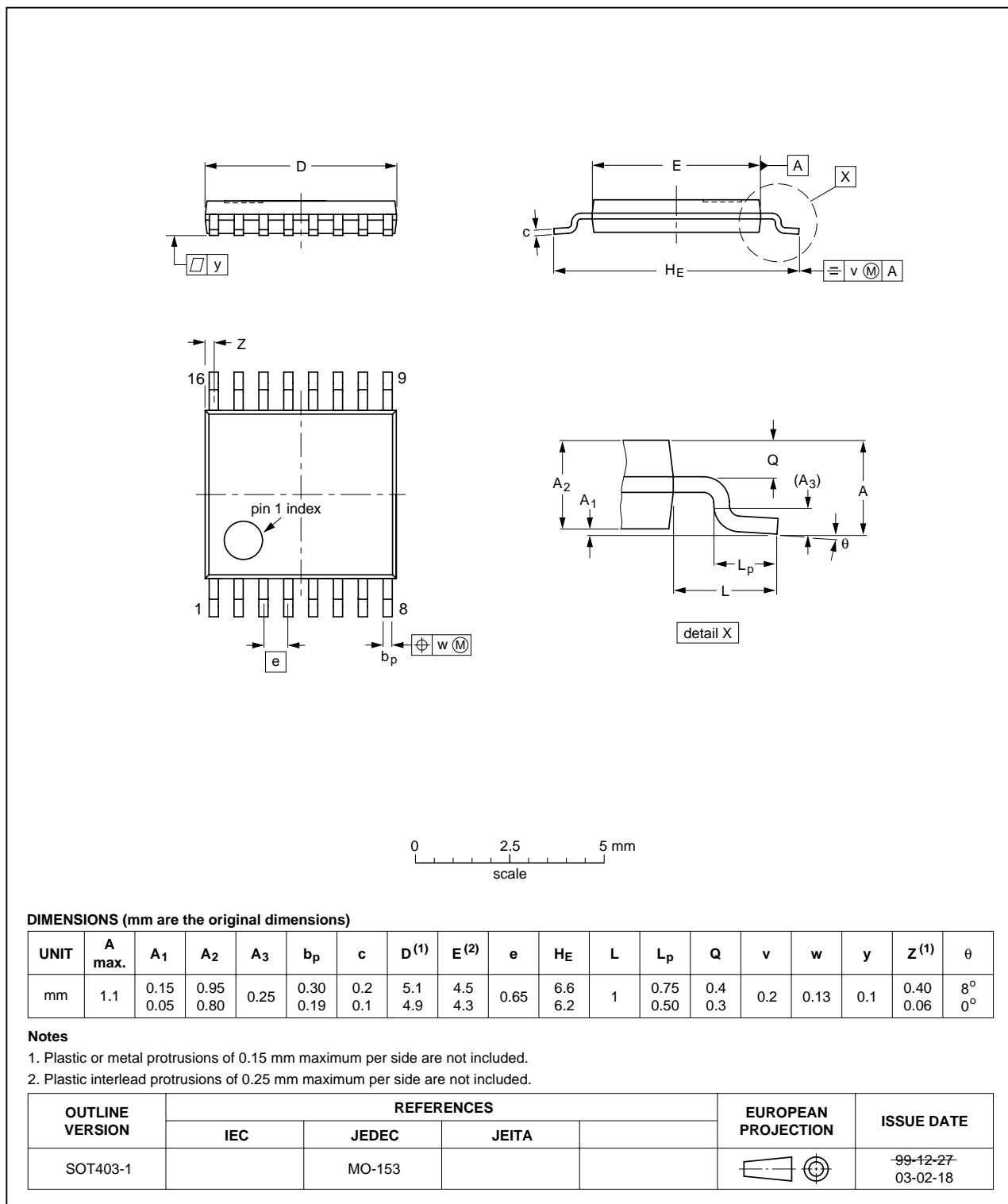


Fig 13. Package outline SOT403-1 (TSSOP16)

15. Abbreviations

Table 10: Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model

16. Revision history

Table 11: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
74LV4020_1	20051129	Product data sheet	-	-	-

17. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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